

TOSHIBA**TC7MZ245FK**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

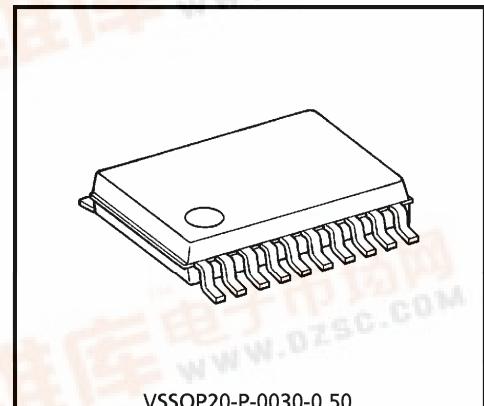
TC7MZ245FK
**LOW VOLTAGE OCTAL BUS TRANSCEIVER
WITH 5V TOLERANT INPUTS AND OUTPUTS**

The TC7MZ245 is a high performance CMOS OCTAL BUS TRANSCEIVER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3 V) V_{CC} applications, but it could be used to interface to 5 V supply environment for both inputs and outputs.

The direction of data transmission is determined by the level of the DIR input. The enable input (\overline{OE}) can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.



VSSOP20-P-0030-0.50

Weight : 0.03 g (typ.)

Features

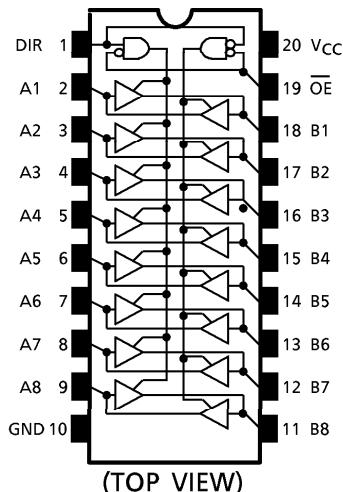
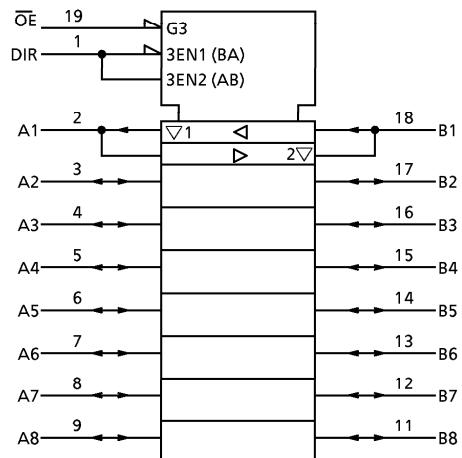
- Low voltage operation : $V_{CC} = 2.0 \sim 3.6$ V
- High speed operation : $t_{pd} = 7.0$ ns (max)
($V_{CC} = 3.0 \sim 3.6$ V)
- Output current : $|I_{OH}| / |I_{OL}| = 24$ mA (min)
($V_{CC} = 3.0$ V)
- Latch-up performance : ± 500 mA
- Available in VSSOP (US20)
- Bidirectional interface between 5 V and 3.3 V signals.
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 245 type.

(Note) : Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

980910EBA1

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury, or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

Pin Assignment**IEC Logic Symbol****Truth Table**

INPUTS		OUTPUTS	FUNCTION	
			A-BUS	B-BUS
L	L	A = B	OUTPUT	INPUT
L	H	B = A	INPUT	OUTPUT
H	X	Z	High Impedance	

X : Don't Care

Z : High Impedance

Maximum Ratings

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7.0	V
DC Input Voltage (DIR, OE)	V _{IN}	-0.5~7.0	V
DC Bus I/O Voltage	V _{I/O}	-0.5~7.0 (Note 1)	V
		-0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	-50	mA
Output Diode Current	I _{OK}	±50 (Note 3)	mA
DC Output Current	I _{OUT}	±50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} /Ground Current	I _{CC} /I _{GND}	±100	mA
Storage Temperature	T _{stg}	-65~150	°C

(Note 1) : Output in Off-State

(Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) : V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Conditions

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage (DIR, OE)	V _{IN}	0~5.5	V
Bus I/O Voltage	V _{I/O}	0~5.5 (Note 5)	V
		0~V _{CC} (Note 6)	
Output Current	I _{OH} /I _{OL}	± 24 (Note 7)	mA
		± 12 (Note 8)	
Operating Temperature	T _{opr}	-40~85	°C
Input Rise And Fall Time	d _t /d _v	0~10 (Note 9)	ns/V

(Note 4) : Data Retention Only

(Note 5) : Output in Off-State

(Note 6) : High or Low State

(Note 7) : V_{CC} = 3.0~3.6 V(Note 8) : V_{CC} = 2.7~3.0 V(Note 9) : V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V**Electrical Characteristics**

DC characteristics (Ta = -40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Min	Max	UNIT
Input Voltage	"H" Level	V _{IH}		2.7~3.6	2.0	—
	"L" Level	V _{IL}		2.7~3.6	—	0.8
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2
				I _{OH} = -12 mA	2.7	2.2
				I _{OH} = -18 mA	3.0	2.4
				I _{OH} = -24 mA	3.0	2.2
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—
				I _{OL} = 12 mA	2.7	—
				I _{OL} = 16 mA	3.0	—
				I _{OL} = 24 mA	3.0	—
Input Leakage Current	I _{IN}	V _{IN} = 0~5.5 V		2.7~3.6	—	± 5.0
3-State Output Off-State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~5.5 V		2.7~3.6	—	± 5.0
Power Off Leakage Current	I _{OFF}	V _{IN} / V _{OUT} = 5.5 V		0	—	10.0
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	10.0
		V _{IN} / V _{OUT} = 3.6~5.5 V		2.7~3.6	—	± 10.0
Increase In I _{CC} Per Input	ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7~3.6	—	500

AC Characteristic (Ta = -40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Min	Max	UNIT
Propagation Delay Time	t _{pLH}	(Fig.1, 2)	2.7	—	8.0	ns
	t _{pHL}		3.3 ± 0.3	1.5	7.0	
Output Enable Time	t _{pZL}	(Fig.1, 3)	2.7	—	9.5	ns
	t _{pZH}		3.3 ± 0.3	1.5	8.5	
Output Disable Time	t _{pLZ}	(Fig.1, 3)	2.7	—	8.5	ns
	t _{pHZ}		3.3 ± 0.3	1.5	7.5	
Output To Output Skew	t _{osLH}	(Note 10)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

(Note 10) : Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHm} - t_{pHn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input t_r = t_f = 2.5 ns, C_L = 50 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Typ.	UNIT
Quiet Output Maximum Dynamic V _{OL}	V _{O LP}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{O LV}	V _{IH} = 3.3 V, V _{IL} = 0 V	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Typ.	UNIT
Input Capacitance	C _{IN}	DIR, OE	3.3	7	pF
Bus Input Capacitance	C _{I/O}	A _n , B _n	3.3	8	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10 MHz (Note 11)	3.3	25	pF

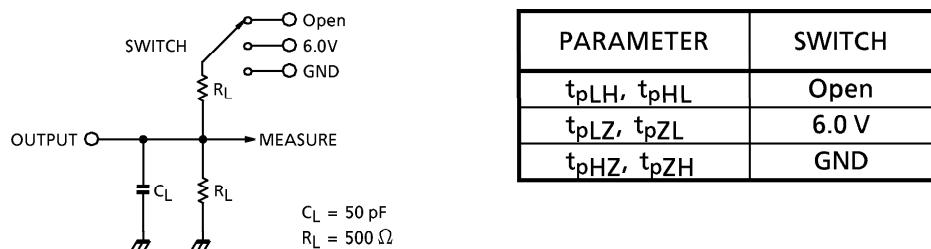
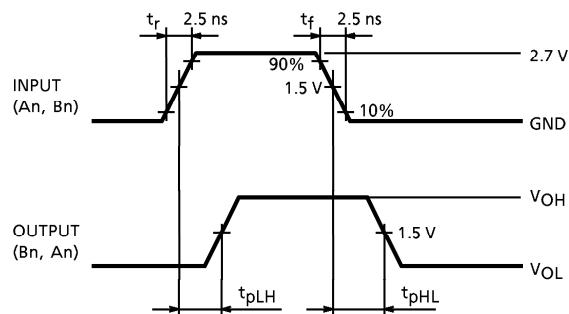
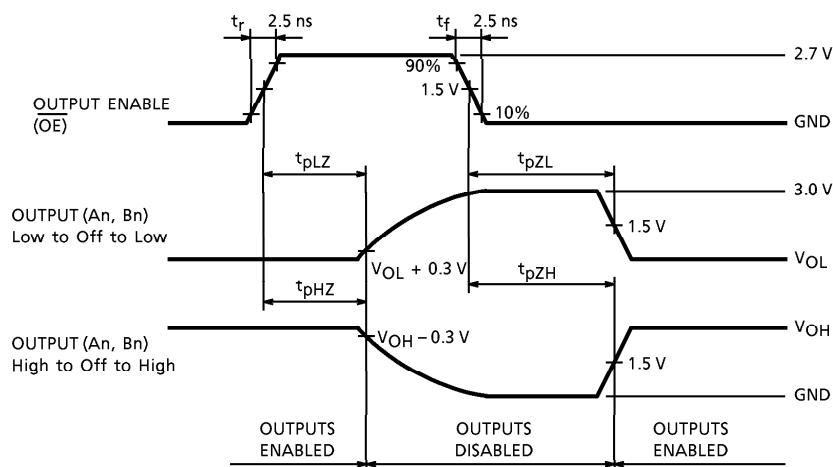
(Note 11) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

Test Circuit

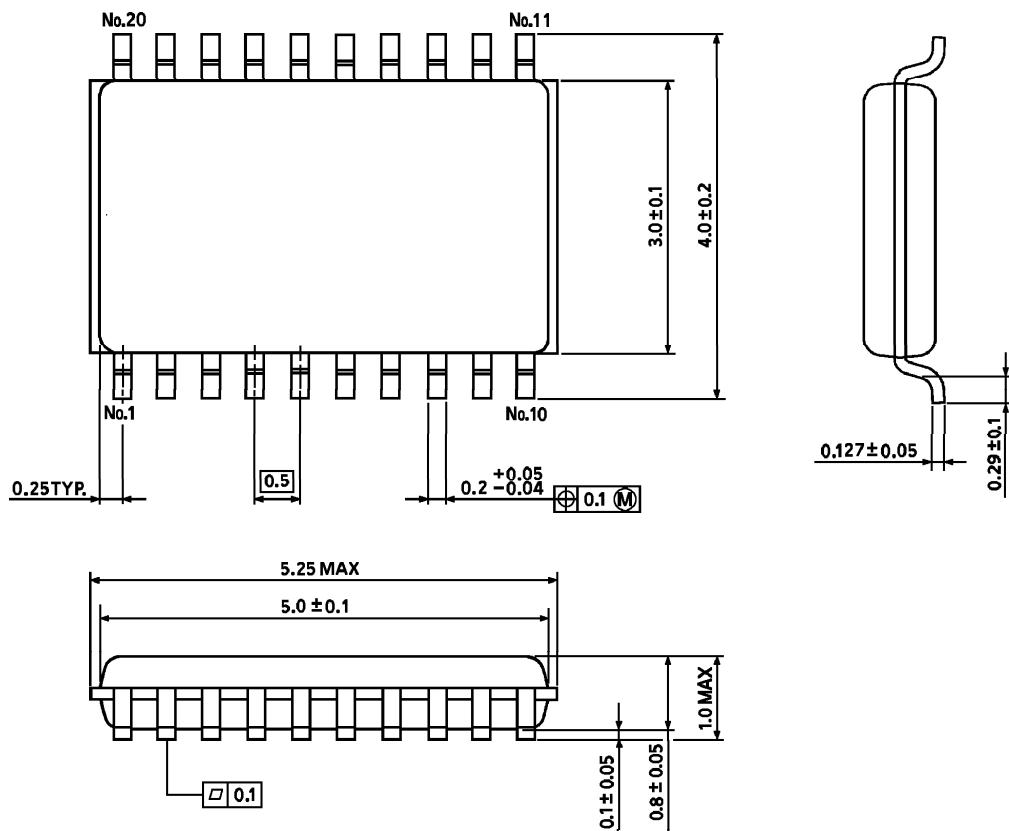
Fig.1

**AC Waveform**Fig.2 t_{pLH}, t_{pHL} Fig.3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$ 

Outline Drawing

VSSOP20-P-0030-0.50

Unit : mm



Weight : 0.03 g (typ.)